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(54) **DISPLAY APPARATUS, DISPLAY PANEL AND MANUFACTURING METHOD THEREOF**

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(71) Applicants: **Chengdu BOE Optoelectronics Technology Co., Ltd.**, Chengdu, Sichuan (CN); **BOE Technology Group Co., Ltd.**, Beijing (CN)

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(72) Inventors: **Lei DENG**, Beijing (CN); **Yue WEI**, Beijing (CN); **Yanxin SU**, Beijing (CN); **Minghui LI**, Beijing (CN); **Xu YANG**, Beijing (CN)

(57) **ABSTRACT**

(73) Assignees: **Chengdu BOE Optoelectronics Technology Co., Ltd.**, Chengdu, Sichuan (CN); **BOE Technology Group Co., Ltd.**, Beijing (CN)

A display apparatus, a display panel, and a manufacturing method thereof, relate to the field of display technology. The display panel includes a substrate (SU), a transistor layer (TL), a wiring layer (SD), a flat layer (PLN), and a light emitting layer (OL). The transistor layer (TL) is disposed on a side of the substrate (SU) and includes a storage capacitor (C) and a transistor. The material of the first type of transistor includes silicon, and material of the second type of transistor includes a metal oxide. The wiring layer (SD) is disposed on a side of the transistor layer (TL) away from the substrate (SU) and connected to the transistor layer (TL) to form a plurality of pixel circuits. The wiring layer (SD) includes a data line (DAL) and a first power supply line (VDL). The flat layer (PLN) covers the wiring layer (SD). The light emitting layer (OL) is disposed on the flat layer (PLN) and its light emitting device includes a first electrode (ANO) for shielding light, a light emitting material layer (EL) and a second electrode (CAT). At least one of the first electrode (ANO) overlaps with an active layer of one of the second type of transistor.

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